



**DMP3011SSS** 

### **Product Summary**

BV <sub>DSS</sub>	Rds(on) Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C		
-30V	10mΩ @ V <sub>GS</sub> = -10V	-11A		
	18mΩ @ V <sub>GS</sub> = -4.5V	-8.3A		

# **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power management functions
- DC-DC converters

#### 30V P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features and Benefits**

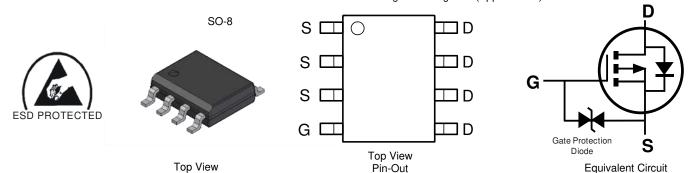
- Low R<sub>DS(ON)</sub> Ensures On-State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/guality/product-definitions/

### **Mechanical Data**

- Package: SO-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074 grams (Approximate)



### Ordering Information (Note 4)

Part Number	Baakaga	Packing		
Part Number	Package	Qty.	Carrier	
DMP3011SSS-13	SO-8	2,500	Tape & Reel	

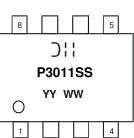
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**





#### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Continuous Drain Current (Note 6) VGS = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-11 -8.8	A
Continuous Drain Current (Note 7) $V_{GS} = -10V$	Steady State	Tc = +25°C Tc = +70°C	ID	-32 -26	А
Maximum Continuous Body Diode Forward Current (Note 8)			Is	-2.4	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			Ідм	-90	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	-90	А
Avalanche Current (Note 8) L = 1mH			las	-14	A
Avalanche Energy (Note 8) L = 1mH			Eas	102	mJ

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	TA = +25°C	PD	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	90	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	68	°C/W
Thermal Resistance, Junction to Case (Note 7)		R <sub>ejc</sub>	8.2	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

						-	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)		0			1		
Drain-Source Breakdown Voltage	BVDSS	-30	_	—	V	$V_{GS} = 0V, I_{D} = -250 \mu A$	
Zero Gate Voltage Drain Current	IDSS		_	-1	μA	$V_{DS} = -24V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>			±10	μA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	-	-3.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance		_	8	10	mΩ	VGS = -10V, ID = -11.5A	
Static Drain-Source On-Resistance	RDS(ON)	_	13	18		VGS = -4.5V, ID = -8.5A	
Diode Forward Voltage	Vsd	_	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	2380	—	pF		
Output Capacitance	Coss		341	_	pF	$\frac{1}{1000} V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	296	—	pF		
Gate Resistance	Rg		3	_	Ω	$V_{DS} = 0V, V_{GS} = 0V,$ f = 1.0MHz	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	_	25	_	nC		
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg		46	_	nC		
Gate-Source Charge	Qgs		6.8	—	nC	$-V_{DS} = -15V, I_{D} = -11.5A$	
Gate-Drain Charge	Qgd		13	_	nC	7	
Turn-On Delay Time	t <sub>D(ON)</sub>		6	—	ns		
Turn-On Rise Time	tR		22	—	ns	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -10V,	
Turn-Off Delay Time	tD(OFF)		43	—	ns	R <sub>G</sub> = 6Ω, I <sub>D</sub> = -11.5A	
Turn-Off Fall Time	tr	_	33	—	ns		
Reverse Recovery Time	trr		19	—	ns		
Reverse Recovery Charge	QRR		8.9	—	nC	Is = -11.5A, dl/dt = 100A/µs	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

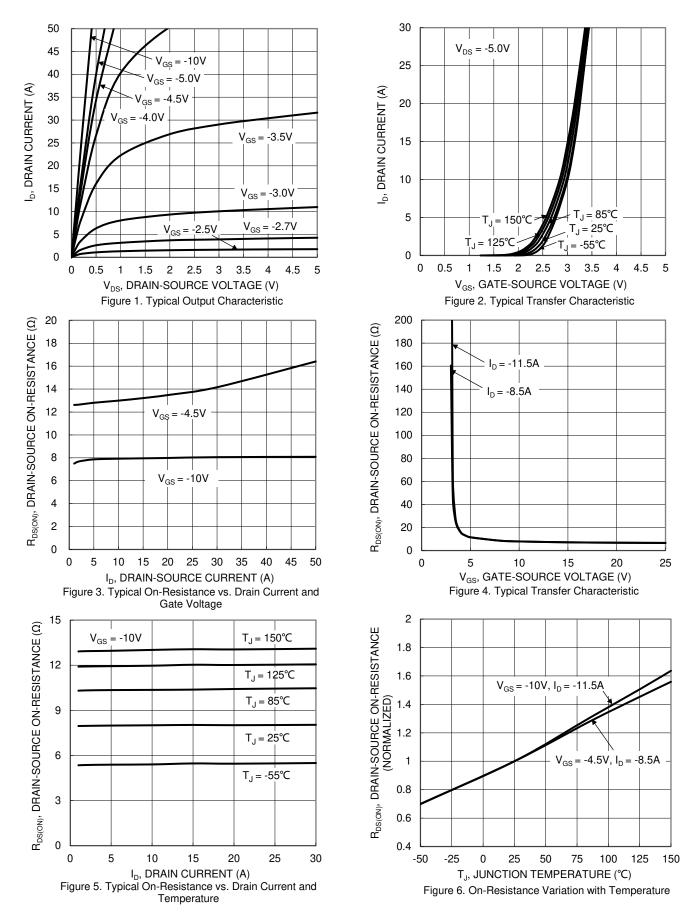
7. Thermal resistance from junction to soldering point (on the exposed drain pad).

8. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ .

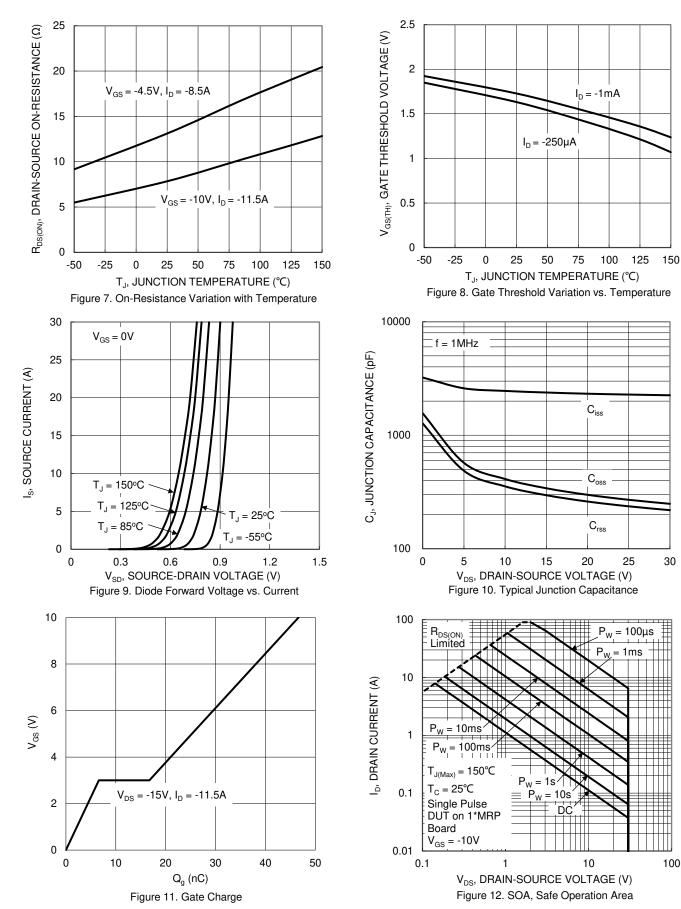
9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.



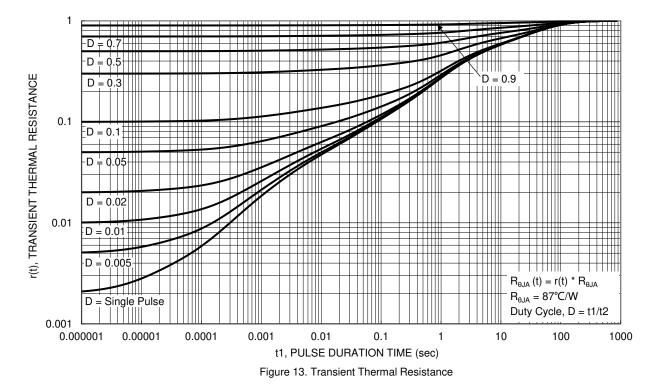






DMP3011SSS Document number: DS43414 Rev. 4 - 2







Тур

1.45

0.15

0.40

0.20

4.90

6.00

3.85

3.90

1.27

0.35

0.72

0.65

Max

1.50

0.50

0.25

4.95

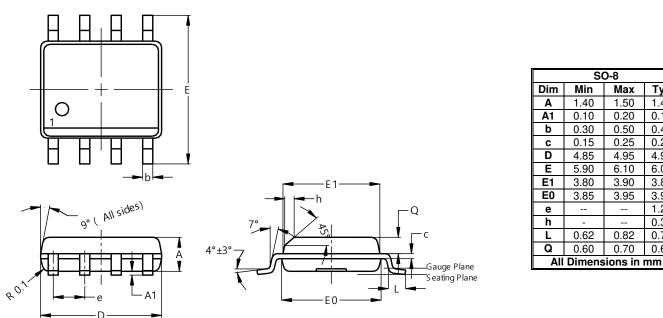
3.90

3.95

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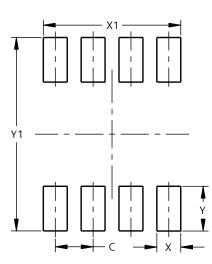
### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.



### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



SO-8

Dimensions	Value (in mm)
С	1.27
Х	0.802
X1	4.612
Y	1.505
Y1	6.50

SO-8



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